Abstract of Disclosure

METHOD OF ETCHING A MULTI-LAYER

A method of etching a multi-layer is provided. The multi-layer includes an aluminum layer disposed on a semiconductor substrate and an anti-reflection coating layer disposed on the aluminum layer. The method includes: performing a first etching process to etch the anti-reflection coating layer by providing a first etching gas, wherein the first etching gas includes a chlorine-containing substance; then performing a second etching process to etch the aluminum layer by providing a second etching gas, wherein the second etching gas does not include a chlorine-containing compound.

Figure 3